Advance Information

Low-Voltage CMOS Quad 2-Input Multiplexer

With 5 V-Tolerant Inputs (Inverting)

The MC74LCX158 is a high performance, quad 2–input inverting multiplexer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX158 inputs to be safely driven from 5 V devices.

Four bits of data from two sources can be selected using the Select and Enable inputs. The four outputs present the selected data in the inverted form. The MC74LCX158 can also be used as a function generator. Current drive capability is 24 mA at the outputs.

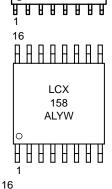
- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Inputs Interface Capability With 5 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



http://onsemi.com

MARKING DIAGRAMS 16 ABBBBBBBBB



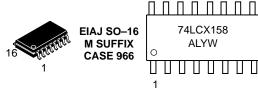


LCX158

AWLYWW



TSSOP-16 DT SUFFIX CASE 948F



= Assembly Location

L, WL = Wafer Lot Y = YearW, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74LCX158D	SO-16	48 Units/Rail
MC74LCX158DR2	SO-16	2500 Units/Reel
MC74LCX158DT	TSSOP-16	96 Units/Rail
MC74LCX158DTEL	TSSOP-16	2000 Units/Reel
MC74LCX158DTR2	TSSOP-16	2500 Units/Reel
MC74LCX158M	EIAJ SO-16	48 Units/Rail
MC74LCX158MEL	EIAJ SO-16	2000 Units/Reel

This document contains information on a new product. Specifications and information herein are subject to change without notice.

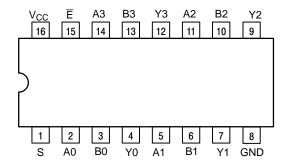


Figure 1. Pinout: 16-Lead Plastic Package (Top View)

PIN NAMES

Pins	Function		
An	Source 0 Data Inputs		
Bn	Source 1 Data Inputs		
Ē	Enable Input		
S	Select Input		
Yn	Outputs		

TRUTH TABLE

Inp	Outputs	
Output Enable	Select	Y0-Y3
Н	Х	Н
L	L	A0-A3
L	Н	B0-B3

X = Don't Care

A0-A3, B0-B3 = The levels of the respective Data-Word Inputs

PIN DESCRIPTIONS

INPUTS

A0-A3 (Pins 2, 5, 11, 14)

Nibble A inputs. The data present on these pins is transferred to the outputs when the Select input is at a low level and the Output Enable input is at a low level. The data is presented to the outputs in inverted form for the LCX158.

B0-B3 (Pins 3, 6, 10, 13)

Nibble B inputs. The data present on these pins is transferred to the outputs when the Select input is at a high level and the Output Enable input is at a low level. The data is presented to the outputs in inverted form for the LCX158.

OUTPUTS

Y0-Y3 (Pins 4, 7, 9, 12)

Data outputs. The selected input nibble is presented at these outputs when the Output Enable input is at a low level.

The data present on these pins is in its inverted form for the LCX158. For the Output Enable input at a high level, the outputs are at a high level for the LCX158.

Select (Pin 1)

Nibble select. This input determines the data word to be transferred to the outputs. A low level on this input selects the A inputs and a high level selects the B inputs.

CONTROL INPUTS

Enable (Pin 15)

Output Enable input. A low level on this input allows the selected data to be presented at the outputs. A high level on this input sets all of the outputs to a high level for the LCX158.

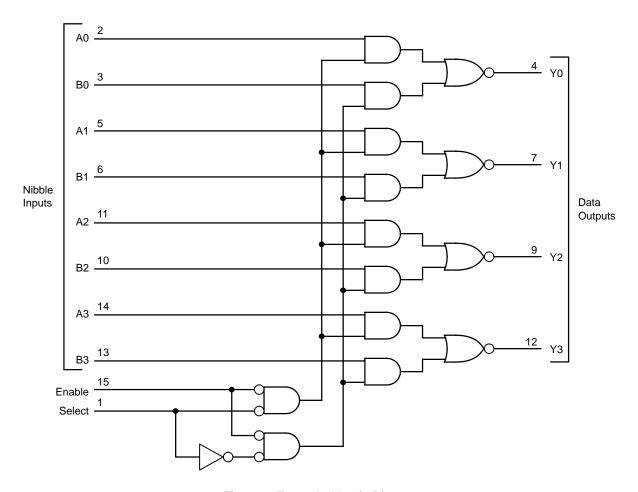


Figure 2. Expanded Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1.)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
lok	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
IO	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.3 to 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage	(HIGH or LOW State) (3–State)	0		V _{CC}	V
ІОН	HIGH Level Output Current	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			-24 -12 -8	mA
l _{OL}	LOW Level Output Voltage	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+24 +12 +8	mA
T _A	Operating Free–Air Temperature		-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{IN} from $V_{CC} = 3.0 \text{ V}$	m 0.8 V to 2.0 V,	0		10	ns/V

^{1.} I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C		
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	Minimum HIGH Level Input Voltage (Note 2.)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V _{CC} ≤ 3.0 V	2.0		
		3.0 V ≤ V _{CC} ≤ 3.6 V	2.0		
V _{IL}	Maximum LOW Level Input Voltage (Note 2.)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V _{CC} ≤ 3.0 V		0.8	
		3.0 V ≤ V _{CC} ≤ 3.6 V		0.8	
V _{OH}	Minimum HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ I}_{OH} = -100 \mu\text{A}$	V _{CC} - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.7		
		$V_{CC} = 2.7 \text{ V; } I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -24 \text{ mA}$	2.2		
V _{OL}	Maximum LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OH} = 100 \mu\text{A}$		0.2	V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = 8 \text{ mA}$		0.7	
		V _{CC} = 2.7 V; I _{OH} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OH} = 16 mA		0.4	
		V _{CC} = 3.0 V; I _{OH} = 24 mA		0.55	
I _I	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5.0	μΑ
I _{CC}	Quiescent Supply Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ V}_{I} = \text{V}_{CC} \text{ or GND}$		10	μΑ
		$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 3.6 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±10	
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{V}_{IH} = \text{V}_{CC} - 0.6 \text{ V}$		500	μΑ

^{2.} These values of V_1 are used to test DC electrical characteristics only.

AC CHARACTERISTICS

			Limits					
			T _A = -40°C to +85°C					
		V _{CC} = 3.0	V ± 3.6 V	V _{CC} =	2.7 V	V _{CC} = 2.3	V to 2.7 V	
		C _L =	50 pF	C _L =	50 pF	C _L =	30 pF	
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Unit
t _{PLH}	Propagation Delay	1.0	6.5	1.0	7.5	1.0	8.5	ns
t _{PHL}	A or B to Y	1.0	6.5	1.0	7.5	1.0	8.5	
t _{PLH}	Propagation Delay	1.0	7.0	1.0	8.0	1.0	9.0	ns
t _{PHL}	S to Y	1.0	7.0	1.0	8.0	1.0	9.0	
t _{PLH}	Propagation Delay	1.0	7.0	1.0	8.0	1.0	9.0	ns
t _{PHL}	Output Enable to Y	1.0	7.0	1.0	8.0	1.0	9.0	
toshl	Output-to-Output Skew		1.0					ns
toslh			1.0					

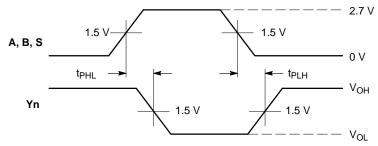
DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 3.)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 3.)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V

^{3.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

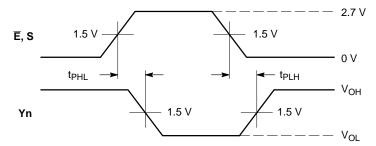
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	7	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF



WAVEFORM 1 – INVERTING PROPAGATION DELAYS

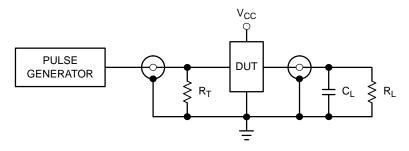
 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



WAVEFORM 2 – INVERTING PROPAGATION DELAYS

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

Figure 3. AC Waveforms



C_L = 50 pF or equivalent (Includes jig and probe capacitance)

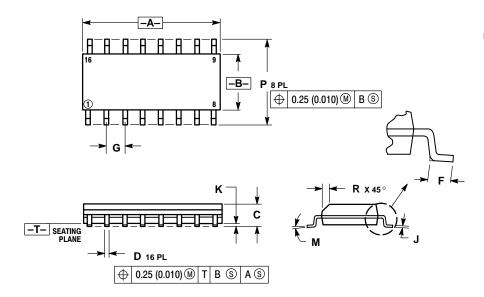
 $R_L = R_1 = 500 \Omega$ or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

PACKAGE DIMENSIONS

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**

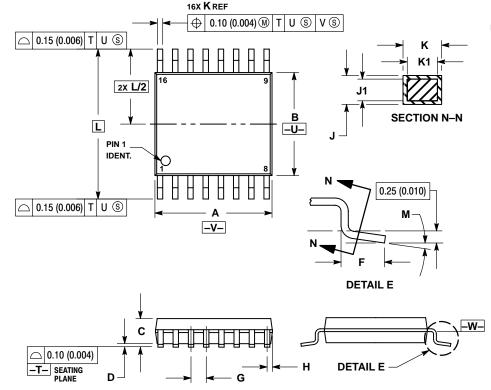


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		MILLIMETERS INCH		HES
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27 BSC		0.050	BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE O**

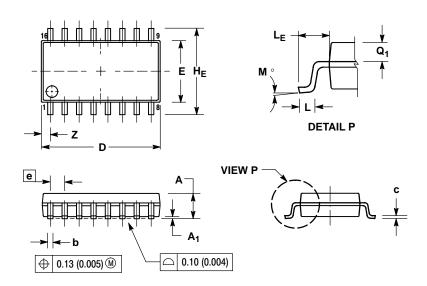


- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD
 FLASH OR PROTRUSION. INTERLEAD FLASH OR
 PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR
- DIMENSION & DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
 MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	0.026 BSC	
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0°	8°	0°	8 °	

PACKAGE DIMENSIONS

EIAJ SO-16 **M SUFFIX** CASE 966-01 **ISSUE O**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.78		0.031

ON Semiconductor and was are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center 4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031

Phone: 81-3-5740-2700 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.